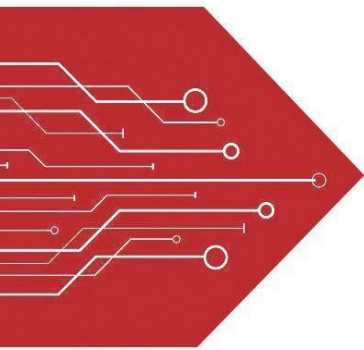


MSKSEMI

SEMICONDUCTOR



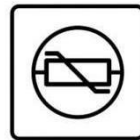
ESD



TVS



TSS



MOV

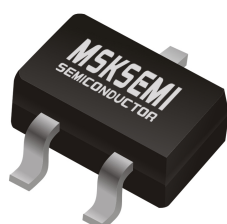
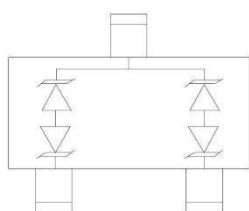


GDT



PLED

Product data sheet


SOT-23

Features

- ◆ 300 Watts peak pulse power ($t_p = 8/20\mu s$)
- ◆ Transient protection for high speed data lines to IEC 61000-4-2 (ESD) $\pm 30kV$ (air), $\pm 30kV$ (contact)
IEC 61000-4-4 (EFT) 40A (5/50ns)
- ◆ Working voltages : 3.3V, 5V, 12V, 15V, 24V
- ◆ Protects two bidirectional line
- ◆ Low operating and clamping voltages
- ◆ Solid-state silicon avalanche technology

Applications

- ◆ Notebooks, Desktops, Servers and Video Graphics Cards
- ◆ USB Power & Data Line Protection
- ◆ Monitors and Flat Panel Displays
- ◆ I²C Bus Protection
- ◆ Portable Instrumentation
- ◆ Set Top Box

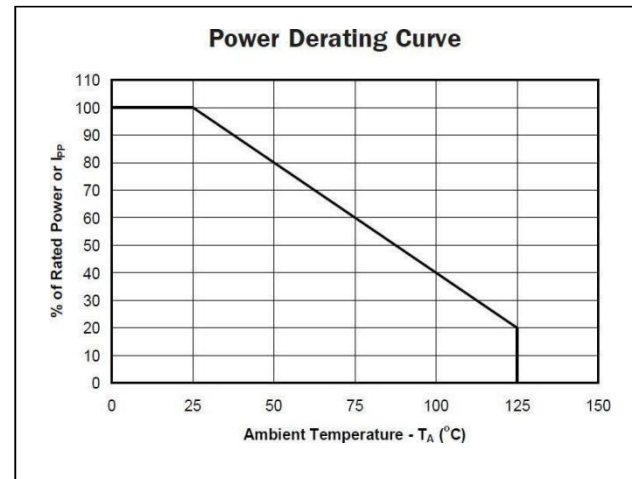
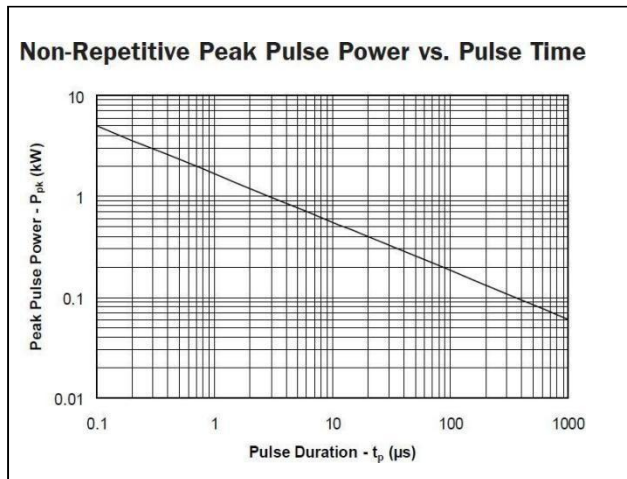
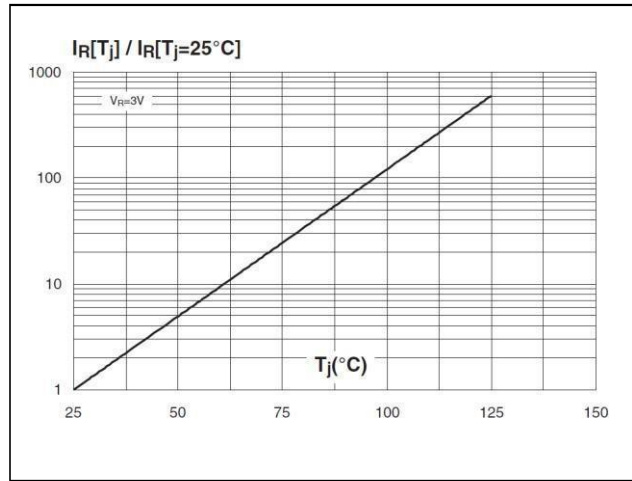
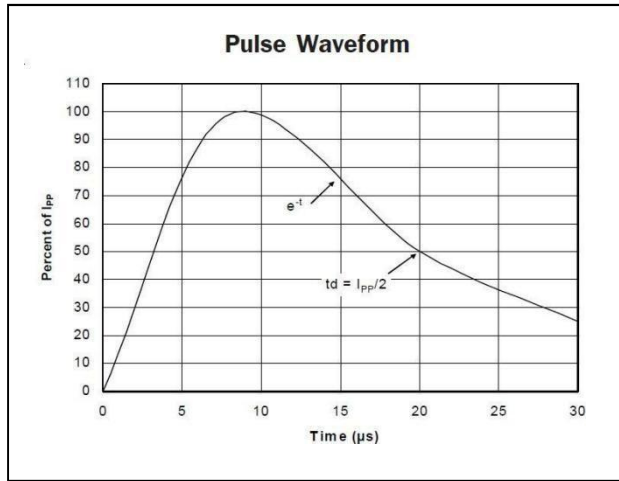
Electrical Characteristics@ $T_a = 25^\circ C$ unless otherwise

P/N	V_{RWM} (V) (max.)	V_B (V) (min.)	I_T (mA)	$V_C@1A$ (V) (max.)	V_C (V) (max.) (@A)		I_R (μA) (max.)	C_T (pF) (max.)
PESD3V3L2BT-MS	3.3	4	1	7.0	14	18	1	100
PESD5V0L2BT-MS	5	6	1	9.8	18	13	1	75
PESD12VL2BT-MS	12	13.3	1	19	32	5	1	20
PESD15VL2BT-MS	15	16.7	1	24	38	5	1	20
PESD24VL2BT-MS	24	26.7	1	43	52	5	1	35

Maximum Rating @ $T_a = 25^\circ C$ unless otherwise specified

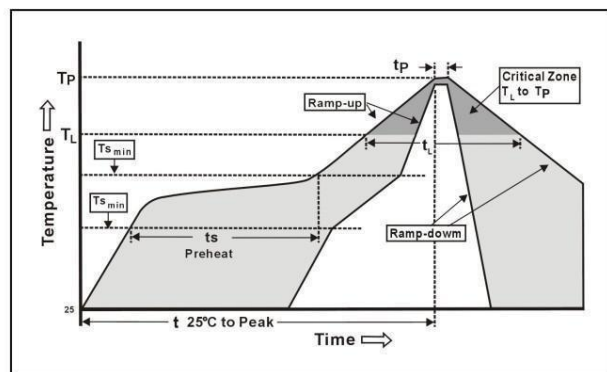
Symbol	Parameter	Ratings	Units
P_{PK}	Peak Pulse Power ($t_p = 8/20\mu s$)	300	Watts
T_L	Lead Soldering Temperature	260(10sec.)	$^\circ C$
T_J	Operating Temperature	-55 to +125	$^\circ C$
T_{STG}	Storage Temperature	-55 to +150	$^\circ C$

Typical Characteristics@ $T_a=25^{\circ}\text{C}$ unless otherwise specified

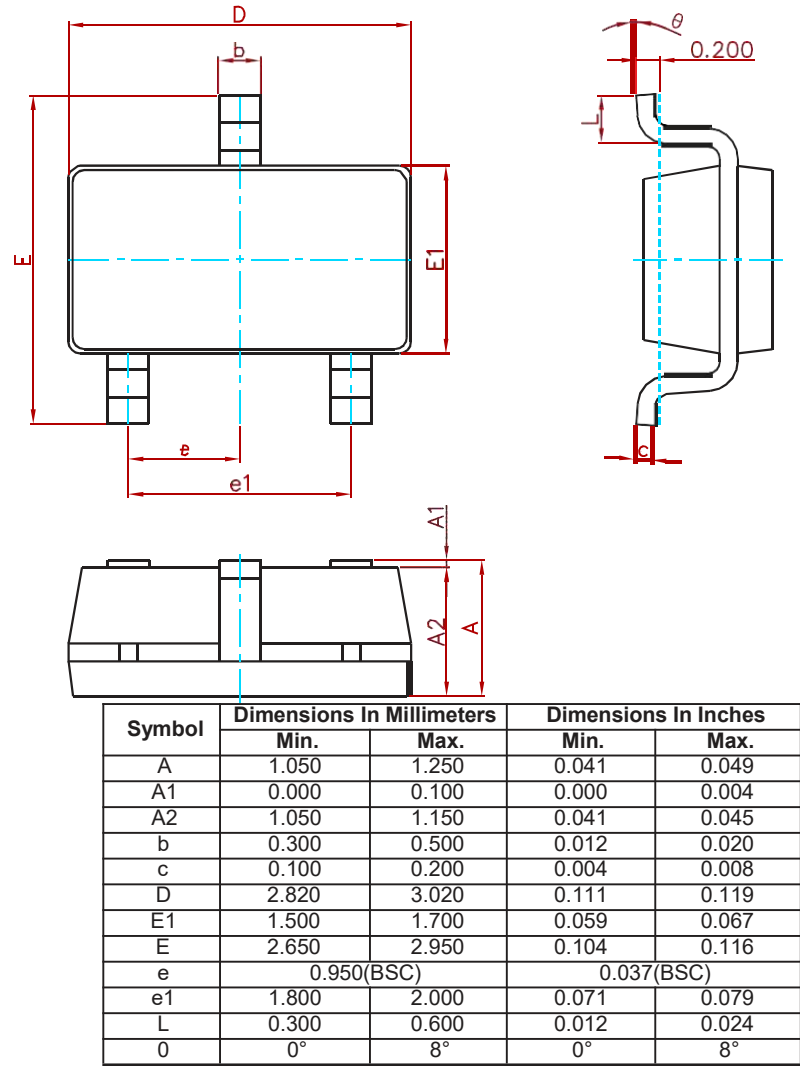


Soldering Parameters

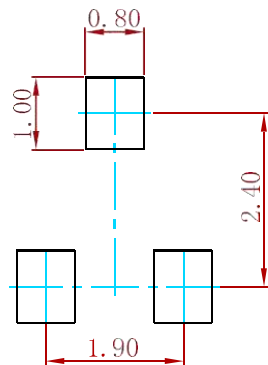
Reflow Condition		Fb – Free assembly
Pre Heat	- Temperature Min ($T_{s(\text{Min})}$)	150°C
	- Temperature Max ($T_{s(\text{Max})}$)	200°C
	- Time (Min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second Max
$T_{s(\text{Max})}$ to T_L - Ramp-up Rate		3°C/second Max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		250 $^{+0/-5}$ °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second Max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		260°C



PACKAGE MECHANICAL DATA



Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
PESDXXXL2BT-MS	SOT-23	3000

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